

## N-Channel 40-V (D-S) MOSFET

### GENERAL DESCRIPTION

The ME4454 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching , and low in-line power loss are needed in a very small outline surface mount package.

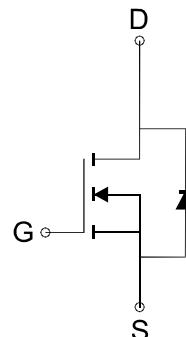
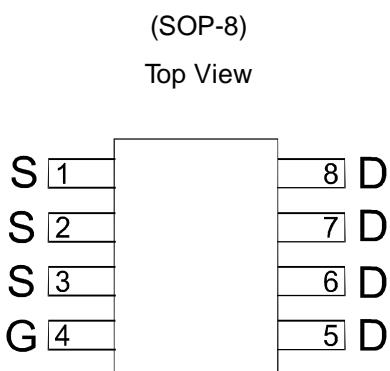
### FEATURES

- $R_{DS(ON)} \leq 13m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} \leq 18m\Omega @ V_{GS}=4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

### APPLICATIONS

- Power Management in Note book
- Battery Powered System
- DC/DC Converter
- Load Switch

### PIN CONFIGURATION



N-Channel MOSFET

Ordering Information: ME4454 (Pb-free)

ME4454-G (Green product- Halogen free)

### Absolute Maximum Ratings ( $T_A=25^\circ C$ Unless Otherwise Noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DSS}$	40	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current( $T_J = 150^\circ C$ )*	$I_D$	10.6	A
		8.5	
Pulsed Drain Current	$I_{DM}$	43	A
Maximum Power Dissipation*	$P_D$	2.5	W
		1.6	
Operating Junction Temperature	$T_J$	-55 to 150	°C
Thermal Resistance-Junction to Ambient*	$R_{\theta JA}$	50	°C/W

\* The device mounted on 1in<sup>2</sup> FR4 board with 2 oz copper



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 Electrical Characteristics ( $T_A = 25^\circ C$  Unless Otherwise Specified)

Symbol	Parameter	Limit	Min	Typ	Max	Unit
<b>STATIC</b>						
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250 $\mu A$	40			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250 $\mu A$	1		3	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V			1	$\mu A$
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance <sup>a</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> = 10A		11	13	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> = 5A		14	18	
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =2.3A, V <sub>GS</sub> =0V		0.7	1.2	V
<b>DYNAMIC</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =10A		28		nC
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =20V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A		14		
Q <sub>gs</sub>	Gate-Source Charge			5.8		
Q <sub>gd</sub>	Gate-Drain Charge			6.5		
C <sub>iss</sub>	Input capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHz		1259		pF
C <sub>oss</sub>	Output Capacitance			139		
C <sub>rss</sub>	Reverse Transfer Capacitance			93		
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DS</sub> =20V, R <sub>L</sub> =20Ω V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =1A		18		ns
t <sub>r</sub>	Turn-On Rise Time			11		
t <sub>d(off)</sub>	Turn-Off Delay Time			50		
t <sub>f</sub>	Turn-Off Fall Time			6		

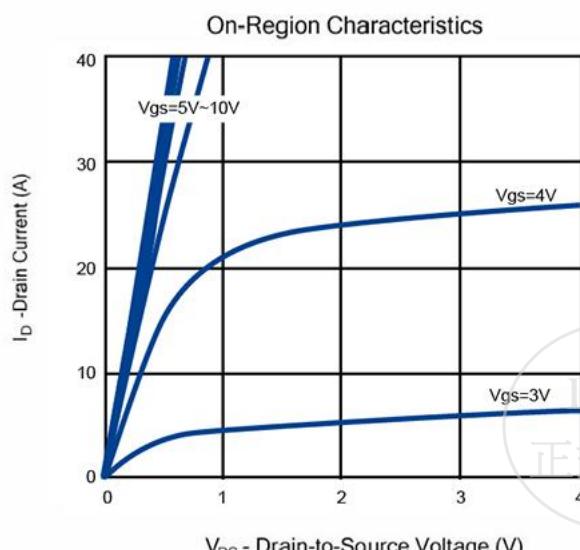
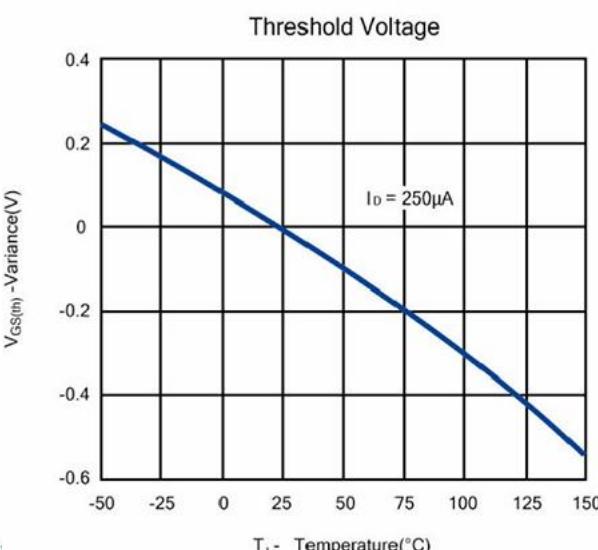
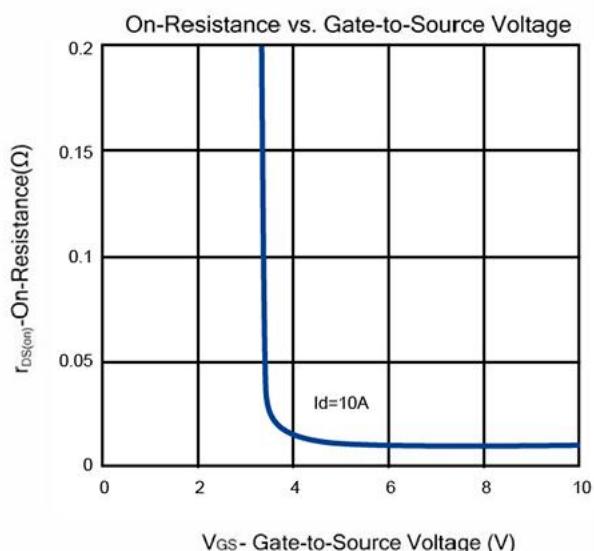
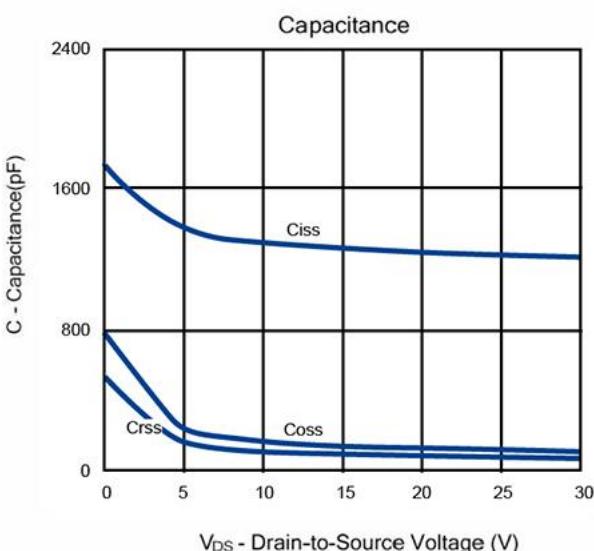
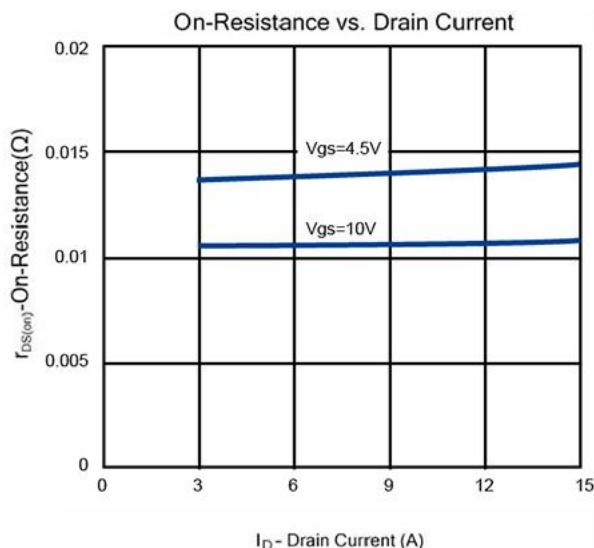
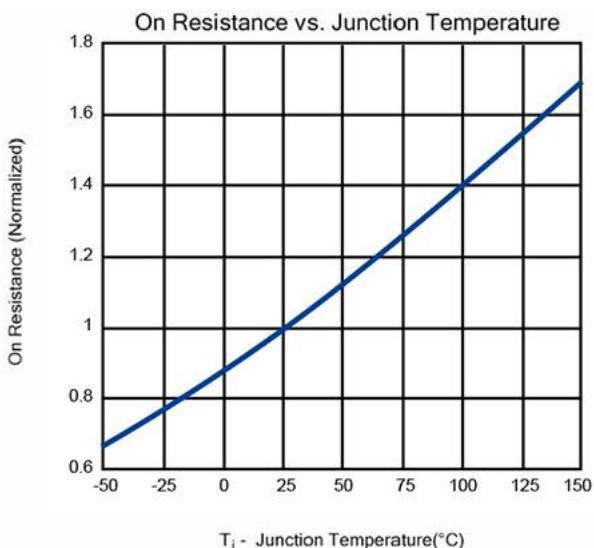
 Notes: a. Pulse test: pulse width  $\leq$  300us, duty cycle  $\leq$  2%, Guaranteed by design, not subject to production testing.

b. Matsuki reserves the right to improve product design, functions and reliability without notice.



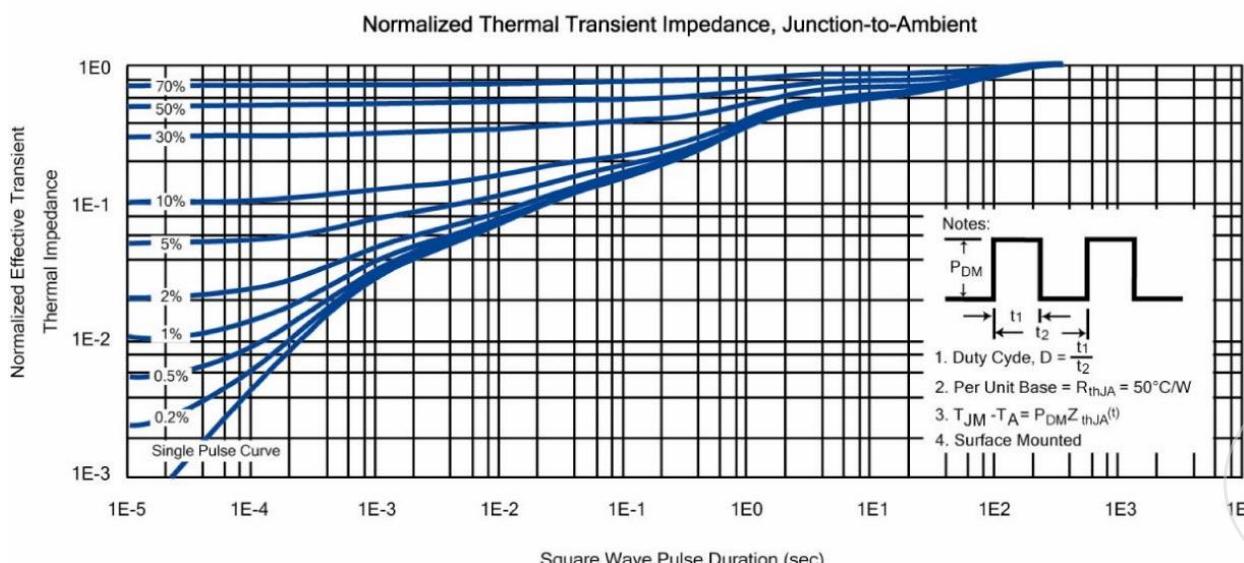
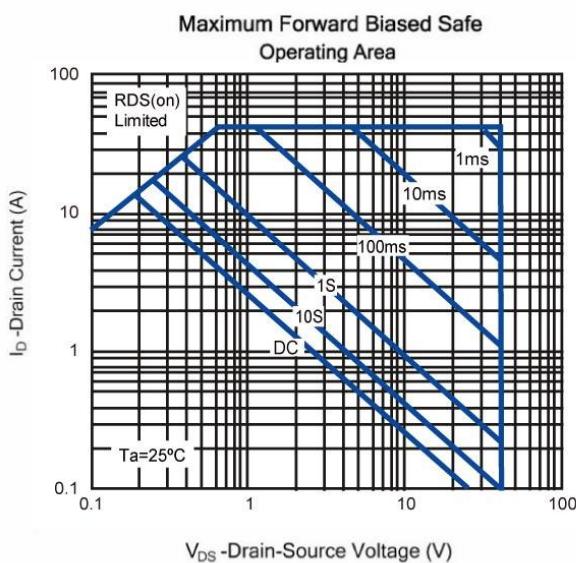
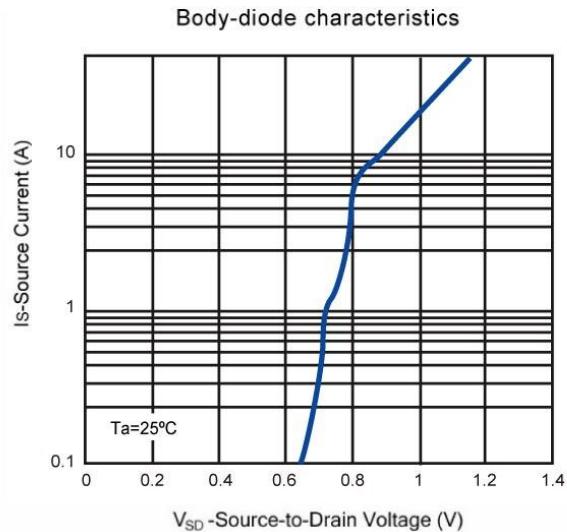
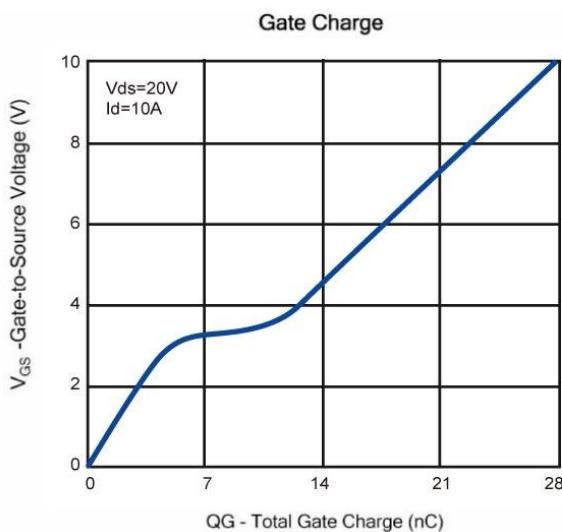
**N-Channel 40-V (D-S) MOSFET**

**Typical Characteristics (T<sub>J</sub> = 25°C Noted)**



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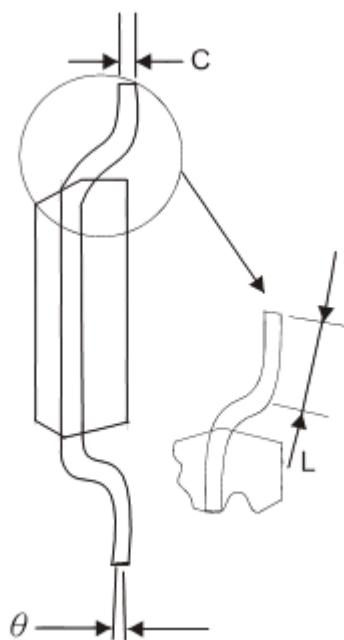
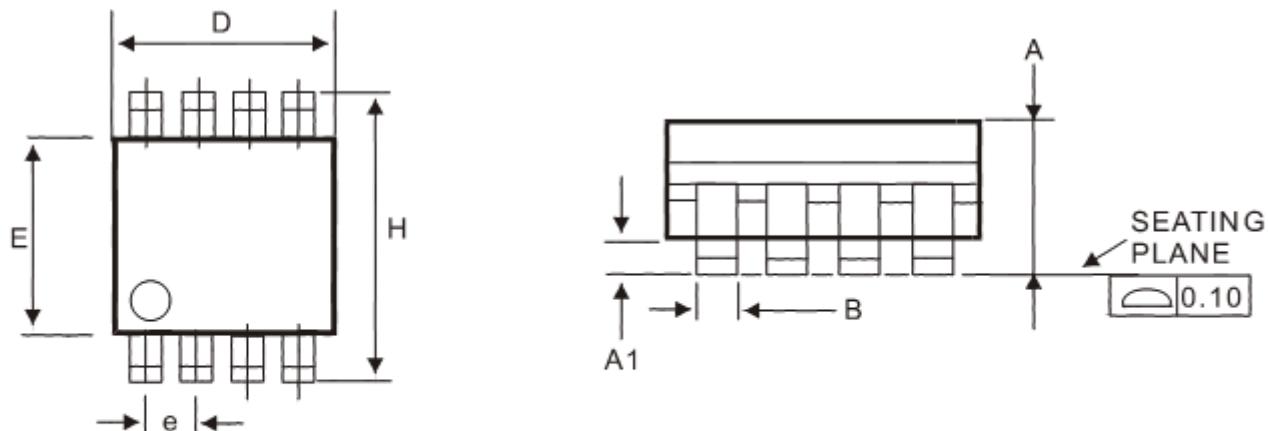
**Typical Characteristics (T<sub>J</sub> = 25°C Noted)**



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### SOP-8 Package Outline



Symbol	MILLIMETERS (mm)	
	MIN	MAX
A	1.35	1.75
A1	0.10	0.25
B	0.35	0.49
C	0.18	0.25
D	4.80	5.00
E	3.80	4.00
e	1.27 BSC	
H	5.80	6.20
L	0.40	1.25
θ	0°	7°



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